

EAST: [10763016 three-contact gate array.wsp:1]

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11: (15) 10 same 4
13: (48) 12 not 11
14: (15283) channel adj block 4
15: (26805) channel adj (block 4 stop 4)
16: (2871) (split 4 wrap 4) adj gate
17: (4145) (split 4 wrap 4 multi) adj gate
18: (28886) (split 4 wrap 4 multi double 4 side 2) adj gate
19: (33) 15 with 18
20: (114) 15 same 18
21: (835) 15 and 18
22: (62) 20 same 8
23: (86816) (float 4 adj (gate electrode plate trap 4) FG) charge 4 adj storage 4
24: (24845) 2 same 23
25: (91169) (wordline "WL" (word digit control adj gate) adj line) (word near (read
26: (104972) (source data) adj line)
27: (882810) (bitline bit adj line readline read adj line sense adj line column)
28: (74091) control adj line
29: (45848) 25 same 27
30: (7160) 26 same 28
31: (341) 24 and 30
32: (5025376) second
33: (3848) 32 adj 8
34: (0) 31 and 33
35: (184) 31 and 9
36: (10826) 24 and 29
37: (720) 38 and 33

DBs: US-PGPUB, USPAT, EPO, JPO, DERWENT, IBM, TDB

Default operator: OR

10 same 4

Nov 2004

DBS form IS&R form Image Text HTML

	U	Inventor	Document#	Issue#	P	Title	Current	Current XR	Retrieval	S	C	P	Image	Doc	P
1		Komori, Kazu	US 5427966	199503		Process for fabricating a semiconductor devi	438/257	257/E23.15						US 542796	
2		Shukuri, Shoj	US 2004018	200409		Semiconductor integrated circuit device and	438/257							US 200401	
3		Hanzawa, Sa	US 2004018	200402		Storage device	365/203							US 200401	
4		Shukuri, Shoj	US 2003019	200319		Semiconductor integrated circuit device and	365/185							US 200301	
5		Yi, Ji-Hye et	US 2003016	200302		Semiconductor memory device having a mult	257/316	257/E21.20						US 200301	
6		Song, Seungh	US 2003013	200301		Scalable two transistor memory device	1/1	257/E21.68						US 200301	
7		Yi, Ji-Hye et	US 2003003	200302		Semiconductor memory device having a mult	438/257	257/311						US 200300	
8		Song, Seungh	US 2002019	200211		SCALABLE TWO TRANSISTOR MEMORY DE	365/63	257/E27.10						US 200201	
9		Song, Seungh	US 6710485	200401		Scalable two transistor memory device	257/316	257/E21.68						US 671048	
10		Yi, Ji-Hye et	US 6686240	200402		Semiconductor memory device having a mult	438/253	257/E21.20						US 668624	

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